

# UT6MC5

#### 60V Nch+Pch Power MOSFET

Symbol	Tr1:Nch	Tr2:Pch
$V_{DSS}$	60V	-60V
R <sub>DS(on)</sub> (Max.)	95mΩ	280mΩ
l <sub>D</sub>	±3.5A	±2.5A
$P_{D}$	2.0	)W

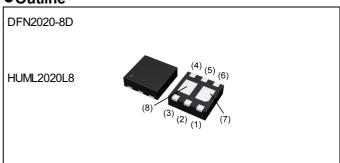
#### Features

- 1) Low on resistance.
- 2) Small Surface Mount Package.
- 3) Pb-free lead plating; RoHS compliant.
- 4) Halogen Free.

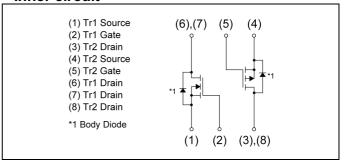
## Application

Switching

#### Outline



#### ●Inner circuit



Packaging specifications

	Packing	Embossed Tape
	Reel size (mm)	180
Туре	Tape width (mm)	8
	Quantity (pcs)	3000
	Taping code	TCR
	Marking	MC5

### ● **Absolute maximum ratings** (T<sub>a</sub> = 25°C ,unless otherwise specified)

Deremeter	Cymbol	Va	lue	Unit
Parameter	Symbol	Tr1:Nch	Tr2:Pch	Offit
Drain - Source voltage	$V_{DSS}$	60	-60	V
Continuous drain current	I <sub>D</sub>	±3.5	±2.5	Α
Pulsed drain current	I <sub>DP</sub> *1	±14	±10	Α
Gate - Source voltage	$V_{GSS}$	±20	±20	V
Avalanche current, single pulse	l <sub>AS</sub> *2	3.5	-2.5	Α
Avalanche energy, single pulse	E <sub>AS</sub> *2	1.0	0.5	mJ
Power dissipation	P <sub>D</sub> *3	2	.0	W
Junction temperature	T <sub>j</sub>	15	50	°C
Operating junction and storage temperature range	T <sub>stg</sub>	-55 to	+150	°C

#### ●Thermal resistance

Parameter	Symbol		Linit		
raidilletei	Symbol	Min.	Тур.	Max.	Unit
Thermal resistance, junction - ambient	R <sub>thJA</sub> *3	-	-	62.5	°C/W

## ● Electrical characteristics (T<sub>a</sub> = 25°C)

Downston	Curanh a l	T	Conditions		Values		Unit	
Parameter	Symbol	Type	Conditions	Min.	Тур.	Max.	Unit	
Drain - Source breakdown	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	Tr1	$V_{GS} = 0V, I_D = 1mA$	60	-	-	V	
voltage	V <sub>(BR)DSS</sub>	Tr2	2 V <sub>GS</sub> = 0V, I <sub>D</sub> = -1mA -60		-	-	V	
Breakdown voltage	ΔV <sub>(BR)DSS</sub>	Tr1	I <sub>D</sub> = 1mA, referenced to 25°C	-	38.9	-	mV/°C	
temperature coefficient	$\Delta T_j$	Tr2	I <sub>D</sub> = -1mA, referenced to 25°C	1	-22	-	IIIV/ C	
Zero gate voltage	_	Tr1	$V_{DS} = 60V, V_{GS} = 0V$	-	-	1		
drain current	I <sub>DSS</sub>	Tr2	$V_{DS} = -60V, V_{GS} = 0V$	-	-	-1	μA	
Gate - Source		Tr1	$V_{GS} = \pm 20V$ , $VDS = 0V$	-	-	±100	A	
leakage current	I <sub>GSS</sub>	Tr2	$V_{GS}$ = ±20V, VDS = 0V	-	-	±100	nA	
Gate threshold	V <sub>GS(th)</sub>	Tr1	$V_{DS} = V_{GS}$ , $I_D = 1mA$	1.0	-	2.5	V	
voltage		Tr2	$V_{DS} = V_{GS}$ , $I_D = -1mA$	-1.0	-	-2.5	V	
Gate threshold voltage	$\Delta V_{GS(th)}$	Tr1	I <sub>D</sub> = 1mA, referenced to 25°C	-	-4.7	-	mV/°C	
temperature coefficient	$\Delta T_j$	Tr2	I <sub>D</sub> = -1mA, referenced to 25°C	1	3.7	-	IIIV/ C	
		Tr1	$V_{GS} = 10V, I_D = 3.5A$	1	73	95		
Static drain - source	D *4	111	$V_{GS} = 4.5V, I_D = 3.5A$	-	104	145	O	
on - state resistance	R <sub>DS(on)</sub> *4	Tr2	$V_{GS} = -10V, I_D = -2.5A$	-	220	280	mΩ	
		112	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -2.5A	-	250	320		
Cata registence	В	Tr1		-	2.7	-	Ω	
Gate resistance	$R_{G}$	Tr2	-	-	14	-	72	
Forward Transfer	IV. 1*4	Tr1	$V_{DS} = 5.0V, I_{D} = 3.0A$	1.2	-	-	S	
Admittance	Y <sub>fs</sub>  *4	Tr2	$V_{DS} = -5.0V, I_{D} = -2.5A$	2.2	-	-		

<sup>\*1</sup> Pw ≤ 10µs, Duty cycle ≤ 1%

Tr2: L  $\simeq$  0.1mH, V<sub>DD</sub> = -30V, R<sub>G</sub> = 25 $\Omega$ , Starting T<sub>j</sub> = 25 $^{\circ}$ C Fig.6-1,6-2

<sup>\*2</sup> Tr1: L  $\simeq$  0.1mH, V<sub>DD</sub> = 30V, R<sub>G</sub> = 25 $\Omega$ , Starting T<sub>j</sub> = 25 $^{\circ}$ C Fig.3-1,3-2

<sup>\*3</sup> Mounted on a Cu board (40×40×0.8mm)

<sup>\*4</sup> Pulsed

## ● Electrical characteristics (T<sub>a</sub> = 25°C)

### <Tr1>

Davamatav	Symbol Conditions		,	Lloit		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	1	135	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 30V	-	38	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	6	-	
Turn - on delay time	t <sub>d(on)</sub> *4	$V_{DD} \simeq 30V$ , $V_{GS} = 10V$	-	5.3	-	
Rise time	t <sub>r</sub> *4	I <sub>D</sub> = 1.75A	-	5.0	-	no
Turn - off delay time	t <sub>d(off)</sub> *4	R <sub>L</sub> = 17.1Ω	-	13.0	-	ns
Fall time	t <sub>f</sub> *4	$R_G = 10\Omega$	-	3.1	-	

#### <Tr2>

Darameter	Symbol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	265	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -30V	-	18	1	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	13	-	
Turn - on delay time	t <sub>d(on)</sub> *4	$V_{DD} \simeq$ -30V, $V_{GS}$ = -10V	-	7.4	-	
Rise time	t <sub>r</sub> *4	I <sub>D</sub> = -1.25A	-	5.0	-	
Turn - off delay time	t <sub>d(off)</sub> *4	$R_L = 24\Omega$	-	42.0	-	ns
Fall time	t <sub>f</sub> *4	$R_G = 10\Omega$	-	18.0	1	

## ●Gate charge characteristics (T<sub>a</sub> = 25°C)

#### <Tr1>

Doromotor	Cumbal	Conditions		Values			Unit
Parameter	Symbol	Condi	Conditions		Тур.	Max.	Offic
	O *4	V <sub>DD</sub> ≃ 30V	V <sub>GS</sub> = 10V	-	3.1	-	
Total gate charge	Q <sub>g</sub> *4			-	1.7	-	~C
Gate - Source charge	Q <sub>gs</sub> *4		V <sub>GS</sub> = 4.5V	-	0.9	-	nC
Gate - Drain charge	Q <sub>gd</sub> *4			-	0.3	1	

#### <Tr2>

Doromotor	Cumabal	Candi	tions	,	1 1 1 1 1 1		
Parameter	Symbol	Conditions		Min.	Тур.	Max.	Unit
	O *4	$V_{DD} \simeq -30V$	V <sub>GS</sub> = -10V	1	6.3	1	
Total gate charge	$\mathbf{Q}_{g}$ .			-	3.2	-	nC
Gate - Source charge	Q <sub>gs</sub> *4	$I_D = -2.5A$	V <sub>GS</sub> = -4.5V	1	1.2	1	IIC
Gate - Drain charge	$Q_{gd}^{*4}$			ı	1.1	ı	

## ●Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

### <Tr1>

Parameter	Symbol Conditions -		Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Continuous forward current	I <sub>S</sub>	T <sub>a</sub> = 25℃	-	-	1.67	^
Pulse forward current	I <sub>SP</sub> *1	1 <sub>a</sub> - 25 C	-	-	14	Α
Forward voltage	V <sub>SD</sub> *4	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.67A	-	-	1.2	V
Reverse recovery time	t <sub>rr</sub> *4	I <sub>S</sub> = 3.5A, V <sub>GS</sub> = 0V	-	23	-	ns
Reverse recovery charge	Q <sub>rr</sub> *4	di/dt = 100A/µs	-	20	-	nC

#### <Tr2>

Parameter	Symbol Conditions		Values			Unit	
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic	
Continuous forward current	I <sub>S</sub>	T <sub>a</sub> = 25°C	-	-	-1.67	^	
Pulse forward current	I <sub>SP</sub> *1	1 <sub>a</sub> - 25 C	-	-	-10	A	
Forward voltage	V <sub>SD</sub> *4	$V_{GS} = 0V, I_{S} = -1.67A$	-	-	-1.2	V	
Reverse recovery time	t <sub>rr</sub> *4	I <sub>S</sub> = -2.5A, V <sub>GS</sub> = 0V	-	22	-	ns	
Reverse recovery charge	Q <sub>rr</sub> *4	di/dt = 100A/μs	-	23	-	nC	

Fig.1 Power Dissipation Derating Curve

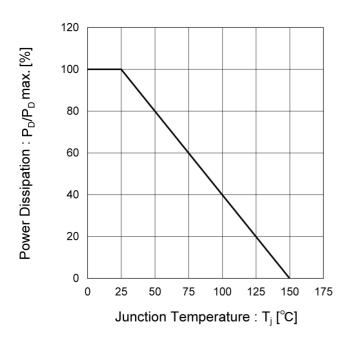
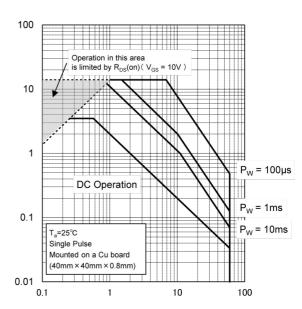


Fig.2 Maximum Safe Operating Area



Drain Current : I<sub>D</sub> [A]

Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

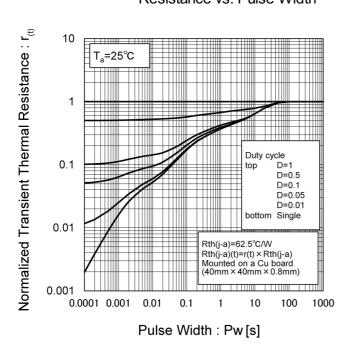


Fig.4 Single Pulse Maximum Power dissipation

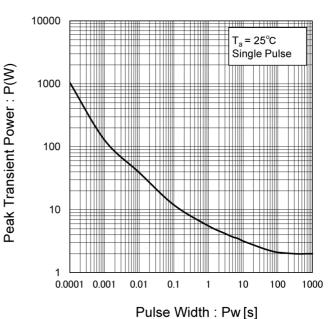


Fig.5 Typical Output Characteristics(I)

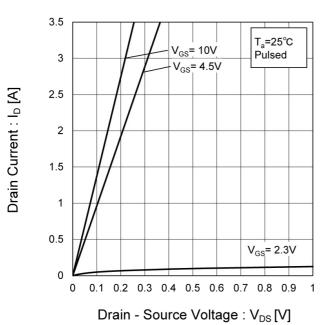
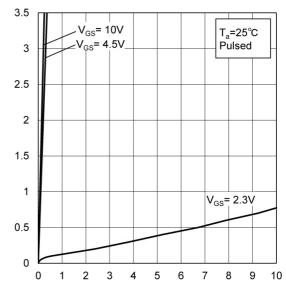


Fig.6 Typical Output Characteristics(II)



Drain Current : I<sub>D</sub> [A]

Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.7 Normalized Breakdown Voltage vs. Junction Temperature

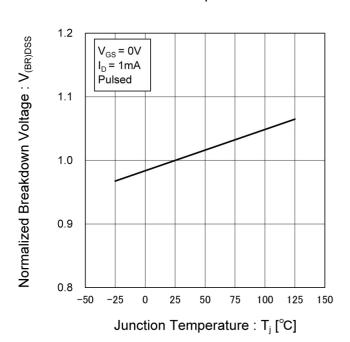


Fig.8 Typical Transfer Characteristics

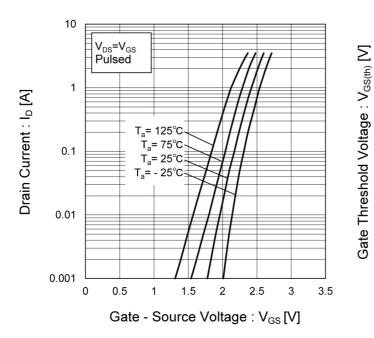


Fig.9 Gate Threshold Voltage vs. Junction Temperature

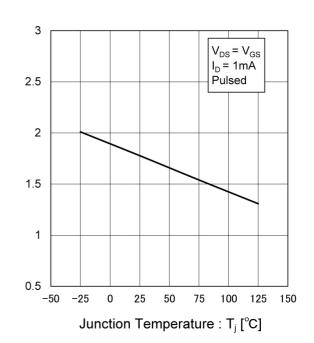


Fig.10 Forward Transfer Admittance vs. Drain Current

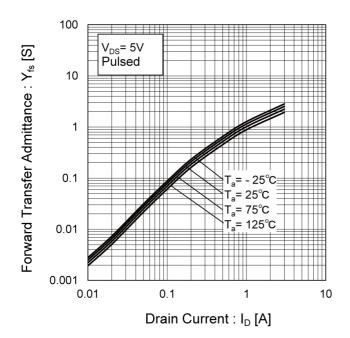


Fig.11 Drain Current Derating Curve

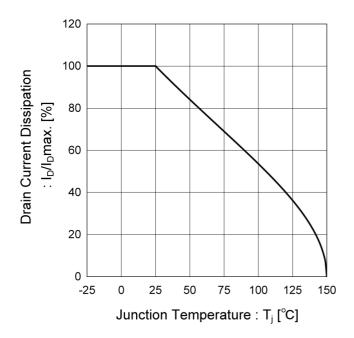


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

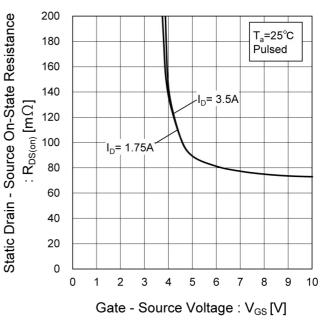


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

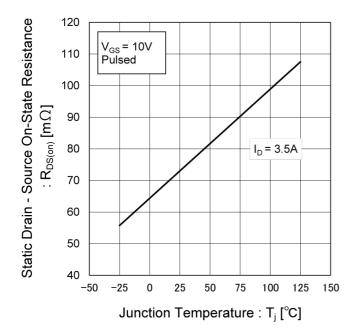


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current(I)

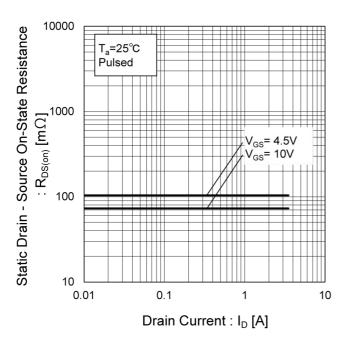


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

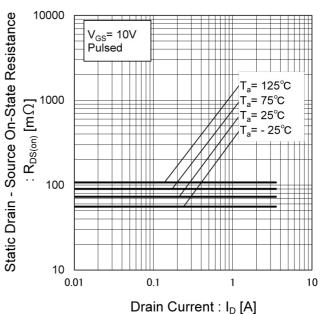


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(III)

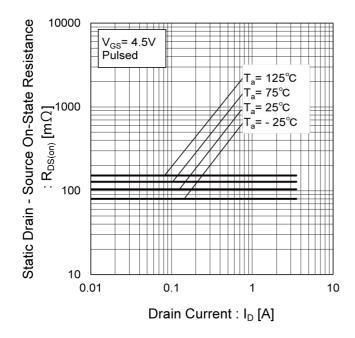


Fig.17 Typical Capacitance vs. Drain - Source Voltage

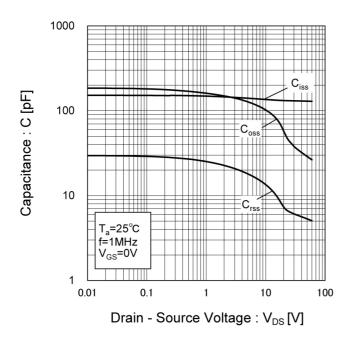


Fig.18 Switching Characteristics

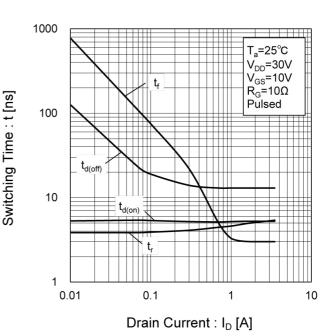


Fig.19 Dynamic Input Characteristics

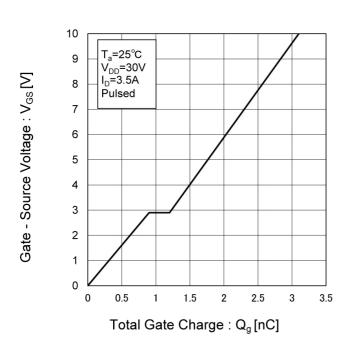
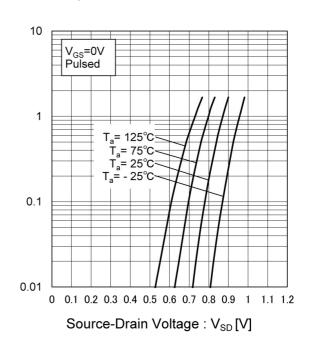


Fig.20 Source Current vs. Source Drain Voltage



Source Current : Is [A]

Fig.1 Power Dissipation Derating Curve

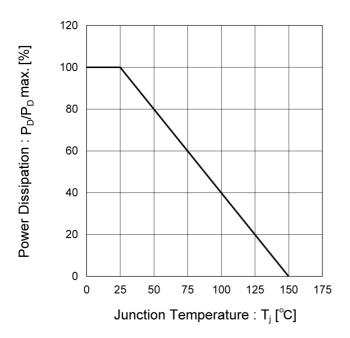
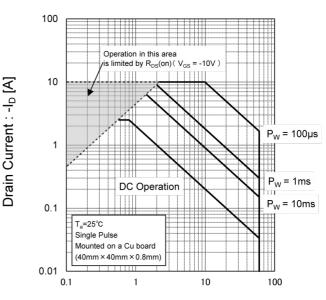


Fig.2 Maximum Safe Operating Area



Drain - Source Voltage : -V<sub>DS</sub> [V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

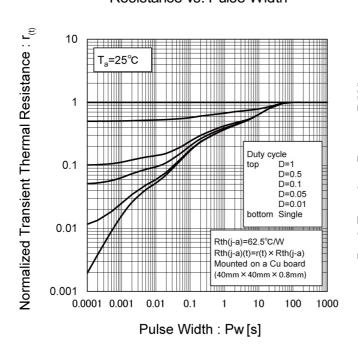


Fig.4 Single Pulse Maximum Power dissipation

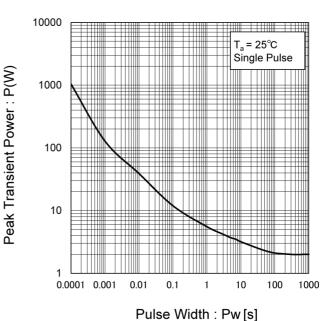


Fig.5 Typical Output Characteristics(I)

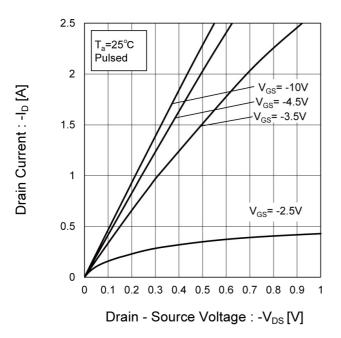


Fig.6 Typical Output Characteristics(II)

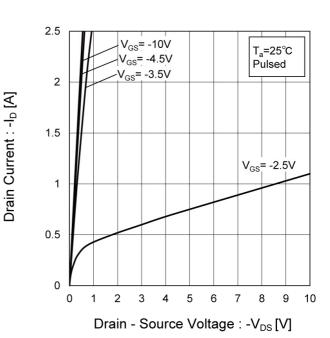


Fig.7 Normalized Breakdown Voltage vs. Junction Temperature

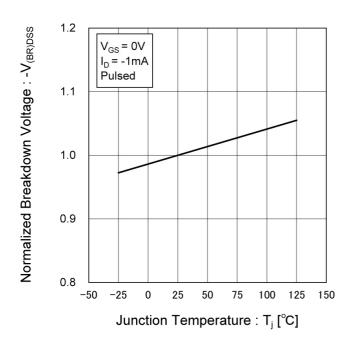


Fig.8 Typical Transfer Characteristics

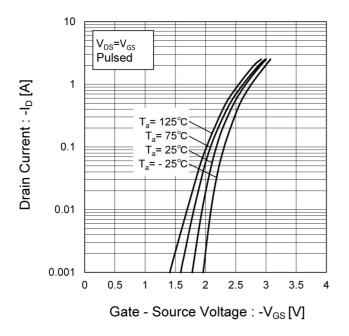


Fig.9 Gate Threshold Voltage vs. Junction Temperature

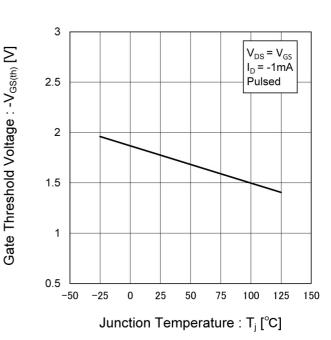


Fig.10 Forward Transfer Admittance vs. Drain Current

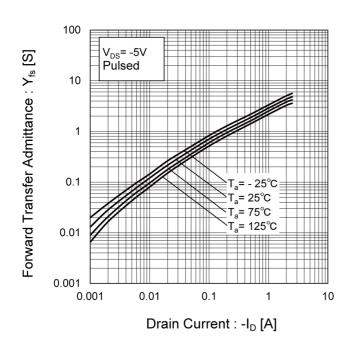


Fig.11 Drain Current Derating Curve

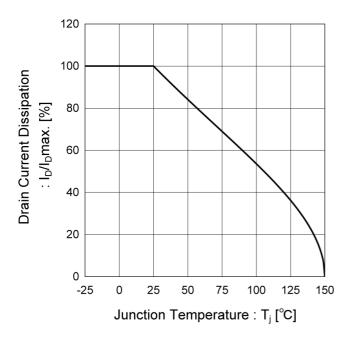


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

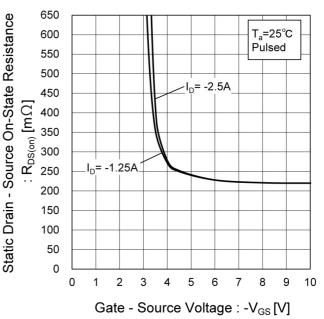


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

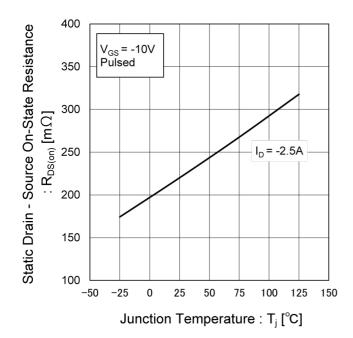


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current(I)

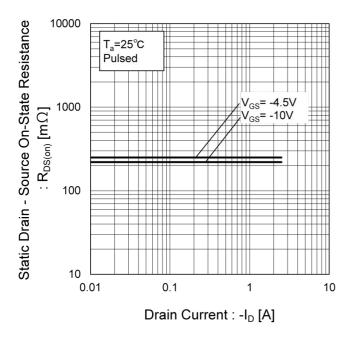


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

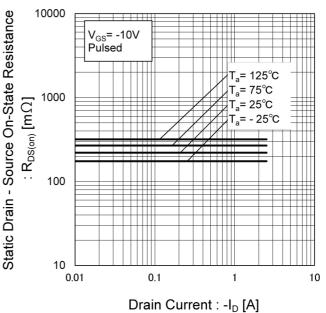
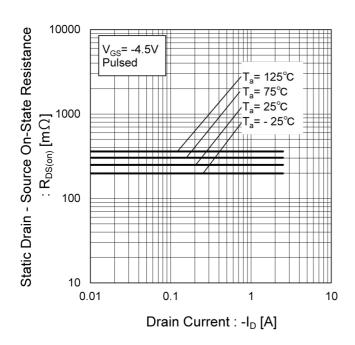


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(III)



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Fig.17 Typical Capacitance vs. Drain - Source Voltage

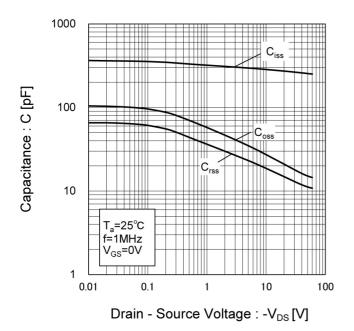


Fig.18 Switching Characteristics

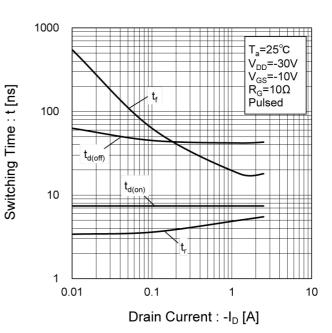


Fig.19 Dynamic Input Characteristics

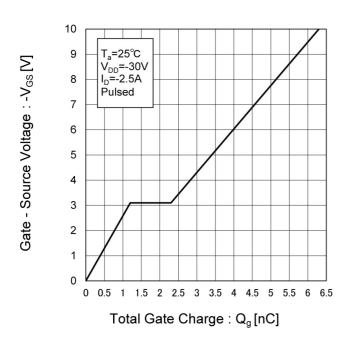
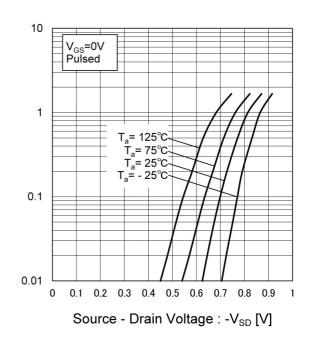


Fig.20 Source Current vs. Source Drain Voltage



Source Current : -I<sub>s</sub> [A]

### ● Measurement circuits < Tr1>

Fig.1-1 Switching Time Measurement Circuit

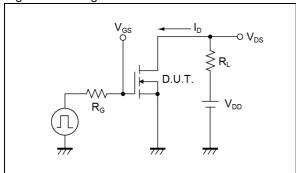


Fig.2-1 Gate Charge Measurement Circuit

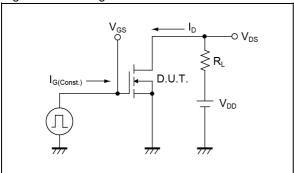


Fig.3-1 Avalanche Measurement Circuit

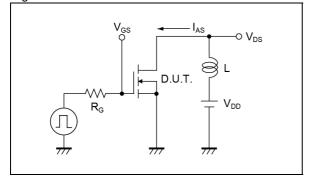


Fig.1-2 Switching Waveforms

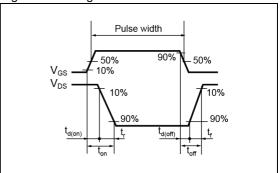


Fig.2-2 Gate Charge Waveform

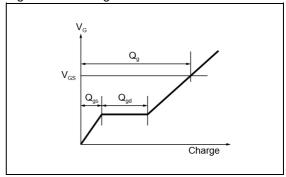
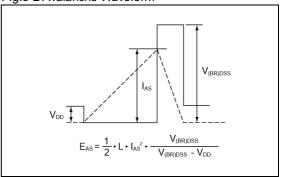


Fig.3-2 Avalanche Waveform



## ● Measurement circuits < Tr2>

Fig.4-1 Switching Time Measurement Circuit

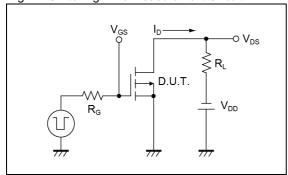


Fig.5-1 Gate Charge Measurement Circuit

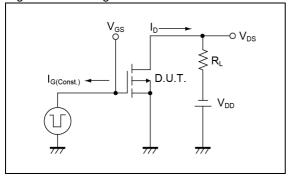


Fig.6-1 Avalanche Measurement Circuit

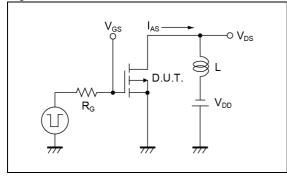


Fig.4-2 Switching Waveforms

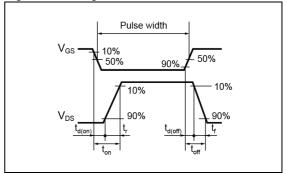


Fig.5-2 Gate Charge Waveform

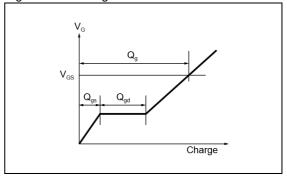
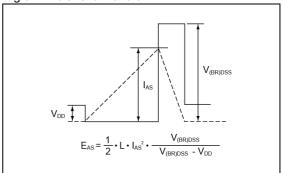


Fig.6-2 Avalanche Waveform

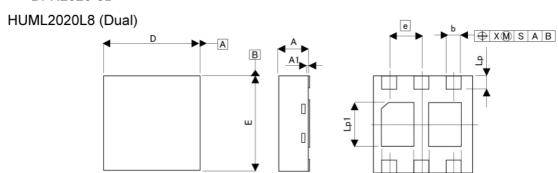


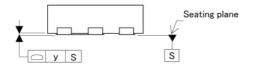
#### Notice

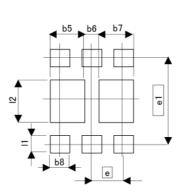
This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

### Dimensions

#### DFN2020-8D







b2 b3 b4 b4

Pattern of terminal position areas [Not a pattern of soldering pads]

	3.411.13.47	TERRO	11.0	LIEO
DIM	MILIME	TERS	INC	HES
Diivi	MIN	MAX	MIN	MAX
Α	0.55	0.65	0.022	0.026
A1	0.00	0.05	0.000	0.002
b	0.25	0.35	0.010	0.014
b1	0.	25	0.0	)10
b2	0.60	0.70	0.024	0.028
b3	0	.3	0.0	)12
b4	0.60	0.70	0.024	0.028
D	1.90	2.10	0.075	0.083
Е	1.90	2.10	0.075	0.083
е	0.	65	0.0	)26
Lp	0.225	0.325	0.009	0.013
Lp1	0.80	1.00	0.031	0.039
х	-	0.10	E-1	0.004
у	-	0.10		0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b5	-	0.70	( <b>-</b>	0.028
b6	0.20	0.30	0.008	0.012
b7	-	0.70	(-	0.028
b8	-	0.45	-	0.018
e1	1.725		0.068	
I1	-	0.425	1.5	0.017
12	-	1.00	1-	0.039

Dimension in mm/inches



## **Notice**

#### **Precaution on using ROHM Products**

1. Our Products are designed and manufactured for application in ordinary electronic equipment (such as AV equipment, OA equipment, telecommunication equipment, home electronic appliances, amusement equipment, etc.). If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment (Note 1), transport equipment, traffic equipment, aircraft/spacecraft, nuclear power controllers, fuel controllers, car equipment including car accessories, safety devices, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.

(Note1) Medical Equipment Classification of the Specific Applications

JÁPAN	USA	EU	CHINA
CLASSⅢ	CL A C C TT	CLASS II b	CL ACCTI
CLASSIV	CLASSⅢ	CLASSⅢ	CLASSⅢ

- 2. ROHM designs and manufactures its Products subject to strict quality control system. However, semiconductor products can fail or malfunction at a certain rate. Please be sure to implement, at your own responsibilities, adequate safety measures including but not limited to fail-safe design against the physical injury, damage to any property, which a failure or malfunction of our Products may cause. The following are examples of safety measures:
  - [a] Installation of protection circuits or other protective devices to improve system safety
  - [b] Installation of redundant circuits to reduce the impact of single or multiple circuit failure
- 3. Our Products are designed and manufactured for use under standard conditions and not under any special or extraordinary environments or conditions, as exemplified below. Accordingly, ROHM shall not be in any way responsible or liable for any damages, expenses or losses arising from the use of any ROHM's Products under any special or extraordinary environments or conditions. If you intend to use our Products under any special or extraordinary environments or conditions (as exemplified below), your independent verification and confirmation of product performance, reliability, etc, prior to use, must be necessary:
  - [a] Use of our Products in any types of liquid, including water, oils, chemicals, and organic solvents
  - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
  - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
  - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (Exclude cases where no-clean type fluxes is used. However, recommend sufficiently about the residue.); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse, is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

#### Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

#### **Precautions Regarding Application Examples and External Circuits**

- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
- 2. You agree that application notes, reference designs, and associated data and information contained in this document are presented only as guidance for Products use. Therefore, in case you use such information, you are solely responsible for it and you must exercise your own independent verification and judgment in the use of such information contained in this document. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of such information.

#### **Precaution for Electrostatic**

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

#### **Precaution for Storage / Transportation**

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
  - [a] the Products are exposed to sea winds or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
  may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is
  exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

#### **Precaution for Product Label**

A two-dimensional barcode printed on ROHM Products label is for ROHM's internal use only.

#### **Precaution for Disposition**

When disposing Products please dispose them properly using an authorized industry waste company.

#### **Precaution for Foreign Exchange and Foreign Trade act**

Since concerned goods might be fallen under listed items of export control prescribed by Foreign exchange and Foreign trade act, please consult with ROHM in case of export.

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